/ Descriptions

PDFN3×3A-8L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

/ Features

V_{DS} (V) = -30V

I_D =-35 A (V_{GS} = ± 20V)

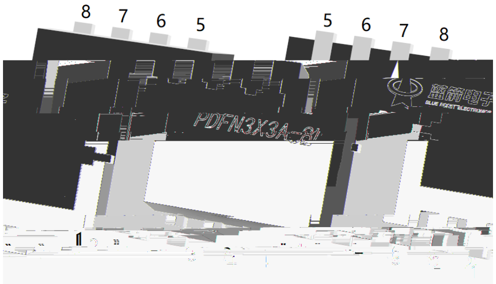
$R_{DS(ON)}$@10V ≤ 12mR(Typ.10mR)

HF Product.

/ Applications

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



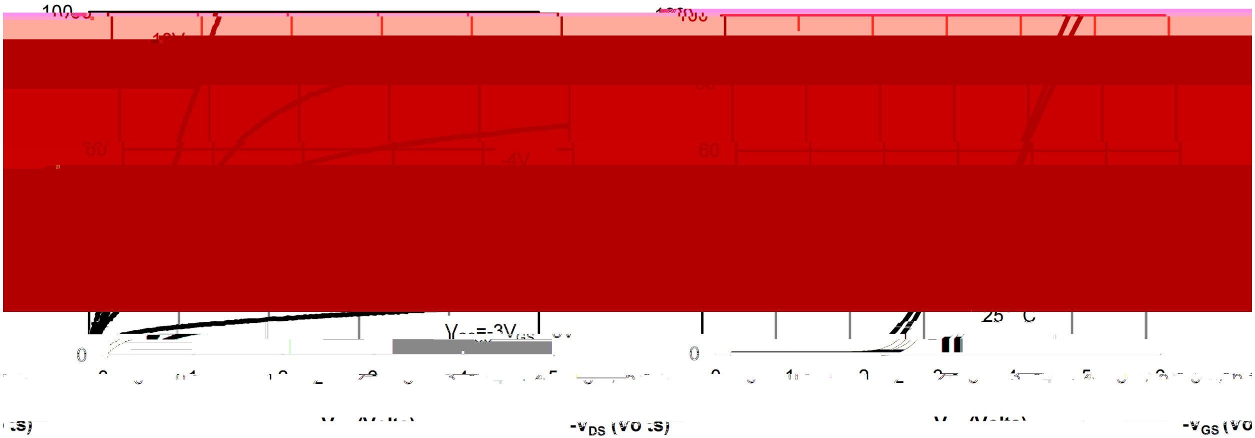
/ Marking

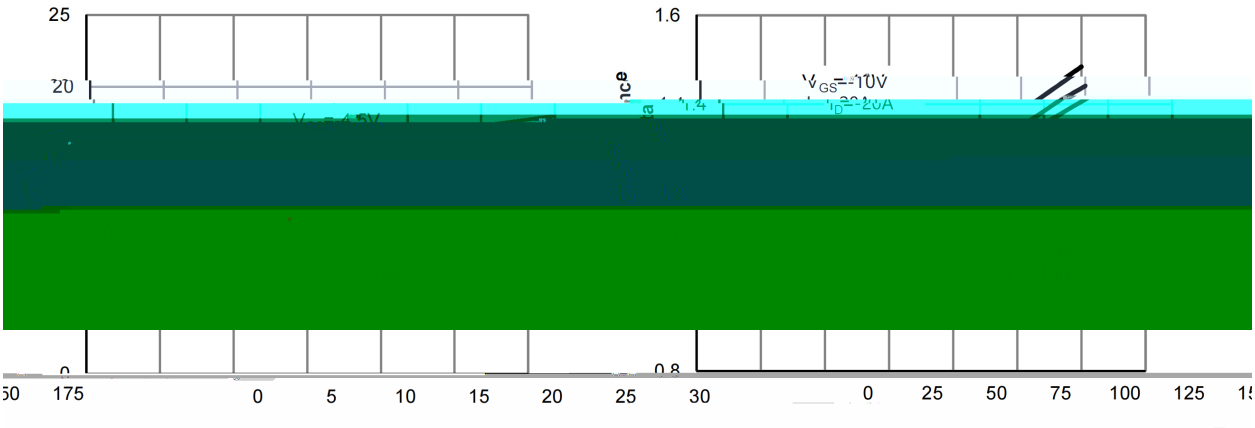
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Drain Current	I_D(Tc=25)		

Parameter Symbol

/ Electrical Characteristic Curve





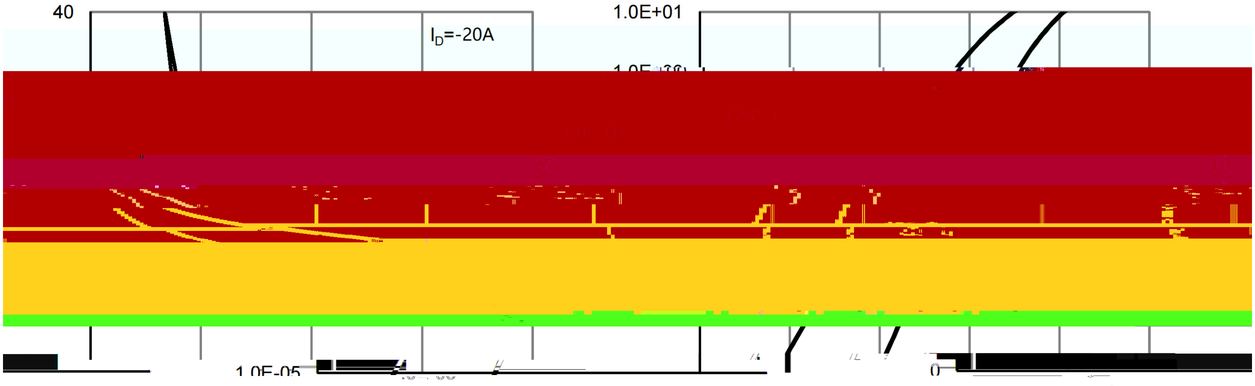
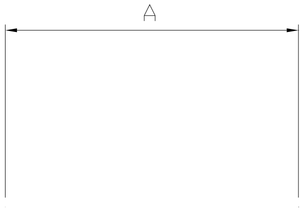


Figure 6: Body Diode Characteristics

/ Package Dimensions

PDFN3X3A-8L

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	3.20	3.30	3.40
A1	3.10	3.15	3.20
B	3.20	3.30	3.40
B1	2.95	3.00	3.05

Rev.00 202011

(   ) / Temperature Profile for IR Reflow Soldering(Pb-Free)